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PAMELA J. SEYMOUR

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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant(s): S. Brad Herner	
Application No.:	Group Art Unit: Unknown
Filed: 12/3/03	Examiner: Unassigned
Title: Use in Semiconductor Devices of Dielectric Antifuses Grown on Silicide	
Attorney Docket No.: MA-070-1	

**INFORMATION DISCLOSURE STATEMENT**

Assistant Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

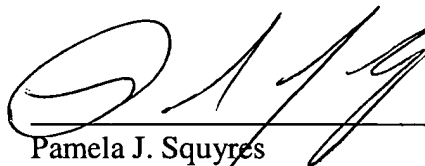
Dear Sir or Madam,

Pursuant to the obligation under 37 CFR § 1.56 and in conformance with 37 CFR §§ 1.97-1.99, Applicant hereby submits documents A1-A15 listed on the attached form PTO-1449 for consideration by the Examiner. Copies of non-patent documents are enclosed herewith. Applicant requests that the Examiner review the entire disclosure of these documents and make them of record.

The filing of this Information Disclosure Statement does not constitute an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 CFR §1.56(b). Further Applicant reserves the right to contest that any of the information submitted herewith is prior art against the present application.

Dated: December 3, 2003

Respectfully submitted,



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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Applicant Number Unknown

Filing Date 12/3/03

First Named Inventor Herner, S. Brad

Group Art Unit Unknown

Examiner Name Unknown

Sheet 1 of 1

Attorney Docket No: MA-070-1

**US PATENT DOCUMENTS**

Examiner Initial *	Cite No	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	A1	10/185507		Vyvoda et al.			06/27/2002
	A2	10/326470		Herner et al.			12/19/2002
	A3	10/440882		Vyvoda			05/19/2003
	A4	10/610804		Herner et al.			06/30/2003
	A5	10/611245		Herner			06/30/2003
	A6	6034882	03/07/2000	Johnson et al.			
	A7	6420215	07/16/2002	Knall et al.			
	A8	6525953	02/25/2003	Johnson			
	A9	6541312	04/01/2003	Vyvoda et al.			

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	A10	CHIANG, STEVE., et al. , "Antifuse Structure Comparison for Field Programmable Gate Arrays", IEDM 92-611, (4/1992), 24.6.1-24.6.4	
	A11	HAMDY, ESMAT., et al. , "Dielectric Based Antifuse for Logic and Memory ICs", IEDM 88, (1988), 786-789	
	A12	HERNER, S..B. , et al. , "Polycrystalline silicon/CoSi2 Schottky diode with integrated SiO2 antifuse: a nonvolatile memory cell", Applied Physics Letters, Volume 82, Number 23, 9 June 2003, (6/9/2003), 4163-4165	
	A13	KONAKOVA, R..V. , et al. , "Ohmic Contacts for Microwave Diodes", Proc. 22nd International Conference on Microelectronics (MIEL 2000), VOL 2, NIS, Serbia, 14-17 May 2000, (1/1999), 477-480	
	A14	SHIH, CHIH-CHING., et al. , "Characterization and Modeling of a Highly Reliable Metal-to-Metal Antifuse for High-Performance and High-Density Field-Programmable Gate Arrays", 1997 IEEE, (9/1997), 25-33	
	A15	WANG, SHOU-EN., et al. , "High-Performance Metal/Silicide Antifuse", IEEE Electron Device Letters, VOL.13, NO 9, September 1992, (9/1992), 471-472	

**EXAMINER****DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional) <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached